

REPLACEMENT PAGE

Please replace page 20 of the original application with the corresponding Amended Sheet under Article 34.

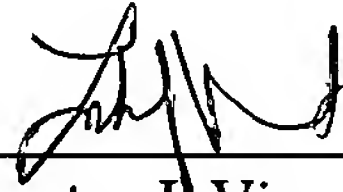
REMARKS

If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: September 15, 2006



Lester J. Vincent
Reg. No. 31,460

12400 Wilshire Blvd.
Seventh Floor
Los Angeles, CA 90025-1026
(408) 720-8300

50. A semiconductor device as claimed in any one of claims 43 to 49, wherein the thermally conductive metal is copper and the epitaxial layers comprise multiple GaN-related epitaxial layers.
- 5 51. A semiconductor device as claimed in any one of claims 43 to 50, wherein the semiconductor device is selected from the group consisting of: a light emitting device, and a transistor device.
- 10 52. A semiconductor device as claimed in any one of claims 43 to 50, wherein the second ohmic contact layer is selected from the group consisting of: blank, and patterned.
- 15 53. A semiconductor device fabricated by the method of any one of claims 1 to 42.